www.DataSheet4U.com

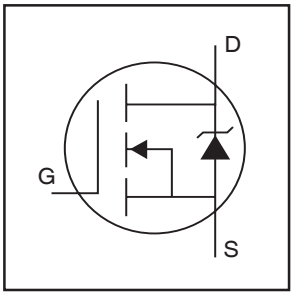
International
IOR Rectifier

PD - 94990

IRFZ24NPbF

HEXFET® Power MOSFET

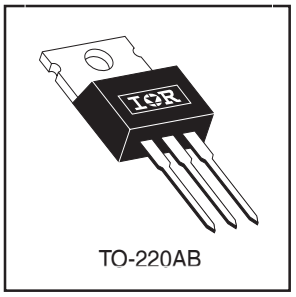
- Advanced Process Technology
- Dynamic dv/dt Rating
- 175°C Operating Temperature
- Fast Switching
- Fully Avalanche Rated
- Lead-Free



V_{DSS} = 55V

$R_{DS(on)}$ = 0.07Ω

I_D = 17A



TO-220AB

Description

Fifth Generation HEXFET® power MOSFETs from International Rectifier utilize advanced processing techniques to achieve the lowest possible on-resistance per silicon area. This benefit, combined with the fast switching speed and ruggedized device design that HEXFET power MOSFETs are well known for, provides the designer with an extremely efficient device for use in a wide variety of applications.

The TO-220 package is universally preferred for all commercial-industrial applications at power dissipation levels to approximately 50 watts. The low thermal resistance and low package cost of the TO-220 contribute to its wide acceptance throughout the industry.

Absolute Maximum Ratings

	Parameter	Max.	Units
I_D @ T_C = 25°C	Continuous Drain Current, V_{GS} @ 10V	17	A
I_D @ T_C = 100°C	Continuous Drain Current, V_{GS} @ 10V	12	
I_{DM}	Pulsed Drain Current ①	68	
P_D @T_C = 25°C	Power Dissipation	45	W
	Linear Derating Factor	0.30	W/°C
V_{GS}	Gate-to-Source Voltage	±20	V
E_{AS}	Single Pulse Avalanche Energy ②	71	mJ
I_{AR}	Avalanche Current①	10	A
E_{AR}	Repetitive Avalanche Energy①	4.5	mJ
dv/dt	Peak Diode Recovery dv/dt ③	5.0	V/ns
T_J	Operating Junction and	-55 to + 175	°C
T_{STG}	Storage Temperature Range		
	Soldering Temperature, for 10 seconds	300 (1.6mm from case)	
	Mounting torque, 6-32 or M3 screw.	10 lbf•in (1.1N•m)	

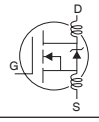
Thermal Resistance

	Parameter	Min.	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case	———	———	3.3	°C/W
$R_{\theta CS}$	Case-to-Sink, Flat, Greased Surface	———	0.50	———	
$R_{\theta JA}$	Junction-to-Ambient	———	———	62	

2/10/04

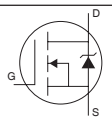
Electrical Characteristics @ T_J = 25°C (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)DSS}$	Drain-to-Source Breakdown Voltage	55	–––	–––	V	V_{GS} = 0V, I_D = 250µA
$\Delta V_{(BR)DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	–––	0.052	–––	V/°C	Reference to 25°C, I_D = 1mA
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	–––	–––	0.07	Ω	V_{GS} = 10V, I_D = 10A ④
$V_{GS(th)}$	Gate Threshold Voltage	2.0	–––	4.0	V	V_{DS} = V_{GS}, I_D = 250µA
g_{fs}	Forward Transconductance	4.5	–––	–––	S	V_{DS} = 25V, I_D = 10A
I_{DSS}	Drain-to-Source Leakage Current	–––	–––	25	µA	V_{DS} = 55V, V_{GS} = 0V
		–––	–––	250		V_{DS} = 44V, V_{GS} = 0V, T_J = 150°C
I_{GSS}	Gate-to-Source Forward Leakage	–––	–––	100	nA	V_{GS} = 20V
	Gate-to-Source Reverse Leakage	–––	–––	-100		V_{GS} = -20V
Q_g	Total Gate Charge	–––	–––	20	nC	I_D = 10A
Q_{gs}	Gate-to-Source Charge	–––	–––	5.3		V_{DS} = 44V
Q_{gd}	Gate-to-Drain ("Miller") Charge	–––	–––	7.6		V_{GS} = 10V, See Fig. 6 and 13 ④
$t_{d(on)}$	Turn-On Delay Time	–––	4.9	–––	ns	V_{DD} = 28V
t_r	Rise Time	–––	34	–––		I_D = 10A
$t_{d(off)}$	Turn-Off Delay Time	–––	19	–––		R_G = 24Ω
t_f	Fall Time	–––	27	–––		R_D = 2.6Ω, See Fig. 10 ④
L_D	Internal Drain Inductance	–––	4.5	–––	nH	Between lead, 6mm (0.25in.) from package and center of die contact
L_S	Internal Source Inductance	–––	7.5	–––		
C_{iss}	Input Capacitance	–––	370	–––	pF	V_{GS} = 0V
C_{oss}	Output Capacitance	–––	140	–––		V_{DS} = 25V
C_{rss}	Reverse Transfer Capacitance	–––	65	–––		f = 1.0MHz, See Fig. 5



Source-Drain Ratings and Characteristics

	Parameter	Min.	Typ.	Max.	Units	Conditions
I_S	Continuous Source Current (Body Diode)	–––	–––	17	A	MOSFET symbol showing the integral reverse p-n junction diode.
I_{SM}	Pulsed Source Current (Body Diode) ①	–––	–––	68		
V_{SD}	Diode Forward Voltage	–––	–––	1.3	V	T_J = 25°C, I_S = 10A, V_{GS} = 0V ④
t_{rr}	Reverse Recovery Time	–––	56	83	ns	T_J = 25°C, I_F = 10A
Q_{rr}	Reverse RecoveryCharge	–––	120	180	nC	di/dt = 100A/µs ④



Notes:

① Repetitive rating; pulse width limited by max. junction temperature. (See fig. 11)

② V_{DD} = 25V, starting T_J = 25°C, L = 1.0mH R_G = 25Ω, I_{AS} = 10A. (See Figure 12)

③ $I_{SD} \leq$ 10A, di/dt ≤ 280A/µs, $V_{DD} \leq V_{(BR)DSS}$, $T_J \leq$ 175°C

④ Pulse width ≤ 300µs; duty cycle ≤ 2%.

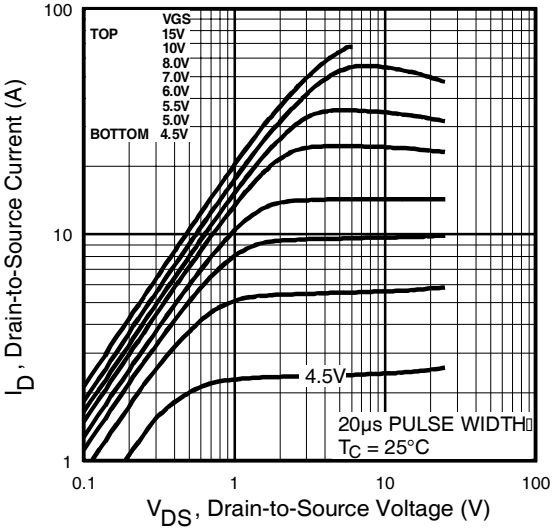


Fig 1. Typical Output Characteristics, T_J = 25ºC

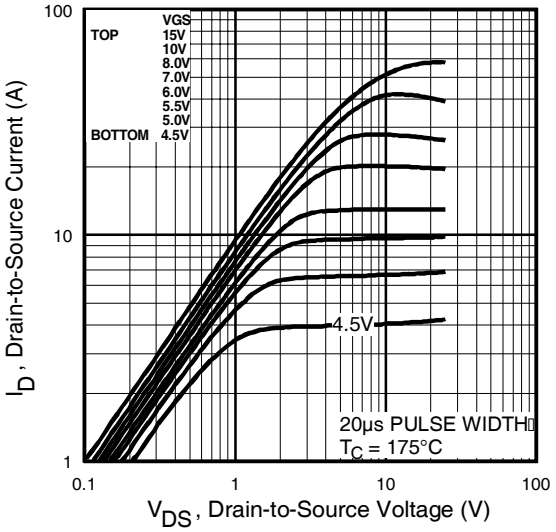


Fig 2. Typical Output Characteristics, T_J = 175ºC

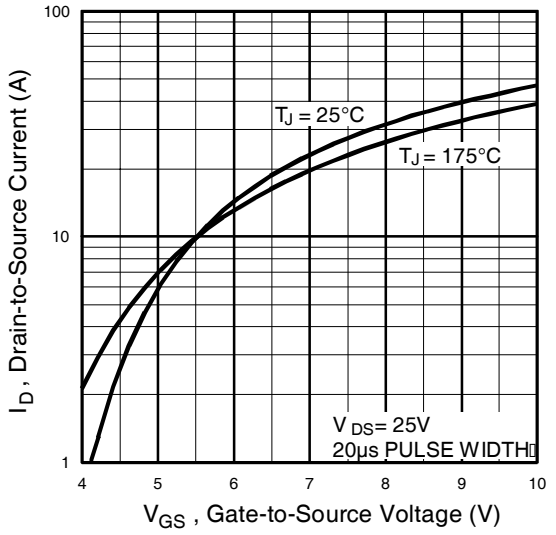


Fig 3. Typical Transfer Characteristics

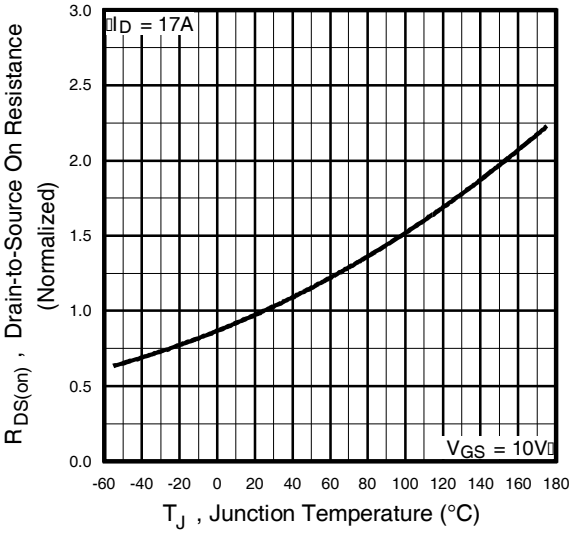


Fig 4. Normalized On-Resistance Vs. Temperature

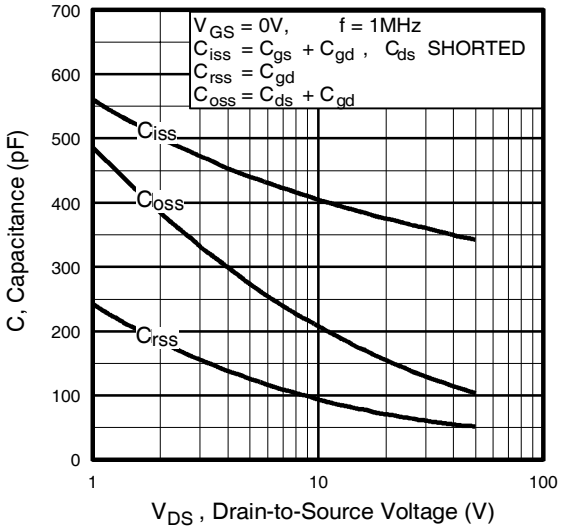


Fig 5. Typical Capacitance Vs. Drain-to-Source Voltage

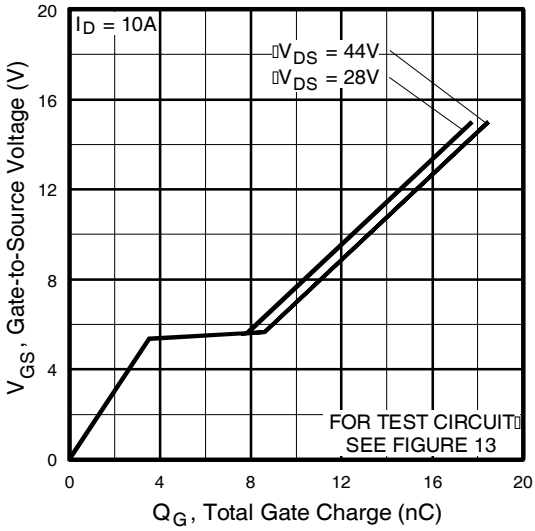


Fig 6. Typical Gate Charge Vs. Gate-to-Source Voltage

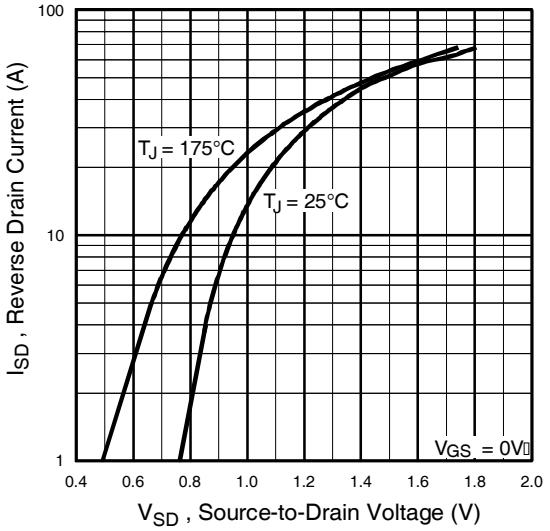


Fig 7. Typical Source-Drain Diode Forward Voltage

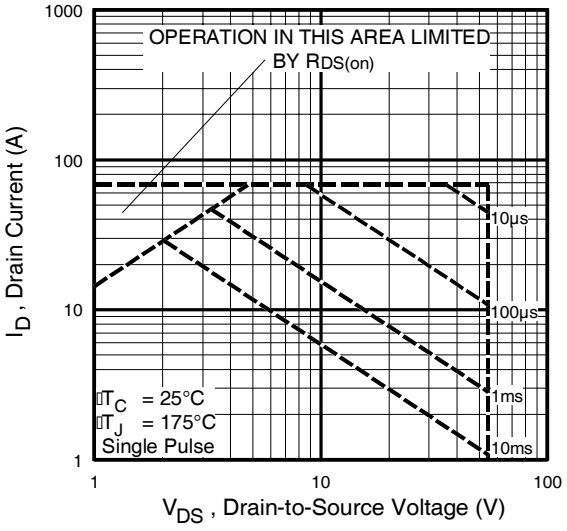


Fig 8. Maximum Safe Operating Area

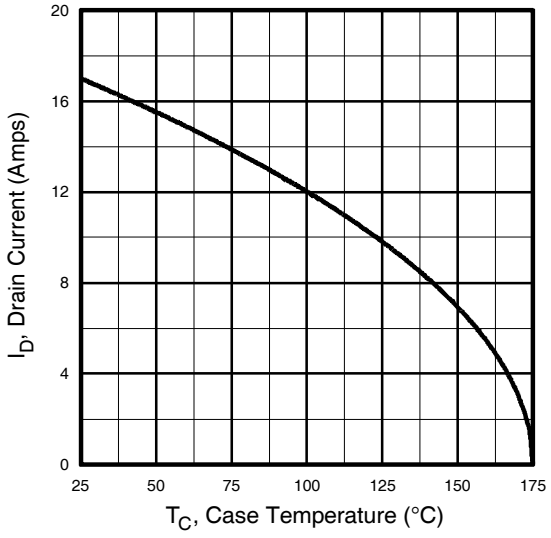


Fig 9. Maximum Drain Current Vs. Case Temperature

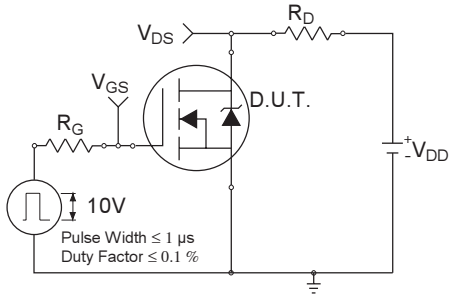


Fig 10a. Switching Time Test Circuit

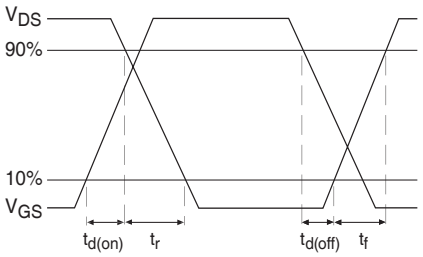


Fig 10b. Switching Time Waveforms

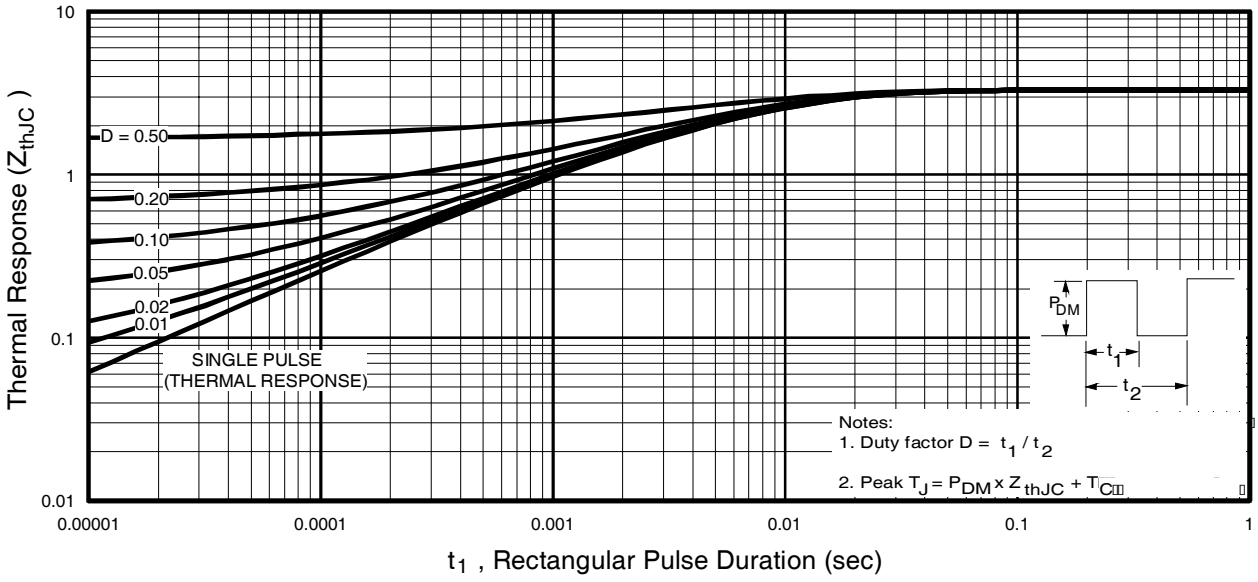


Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Case

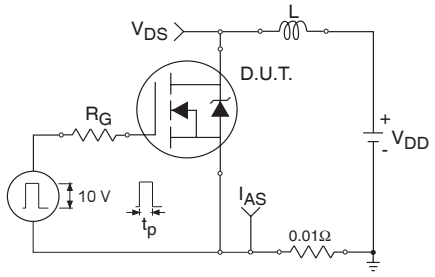


Fig 12a. Unclamped Inductive Test Circuit

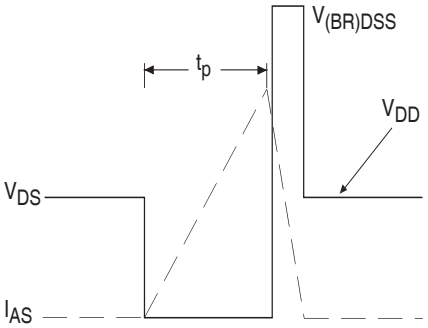


Fig 12b. Unclamped Inductive Waveforms

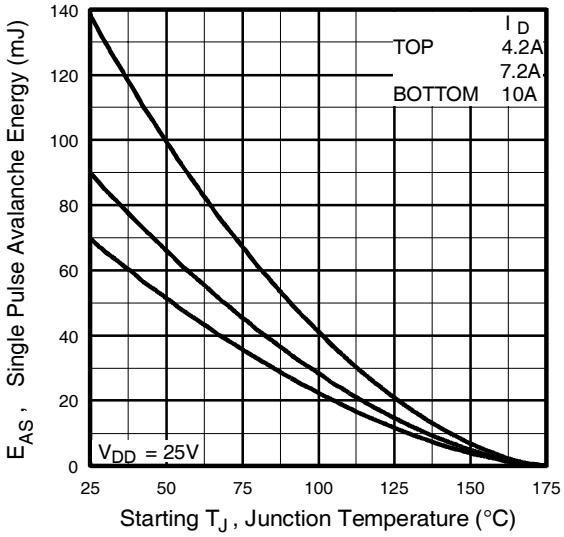


Fig 12c. Maximum Avalanche Energy Vs. Drain Current

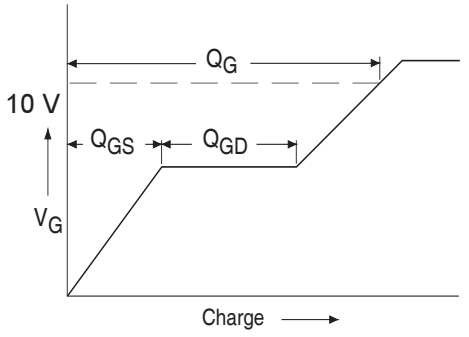


Fig 13a. Basic Gate Charge Waveform

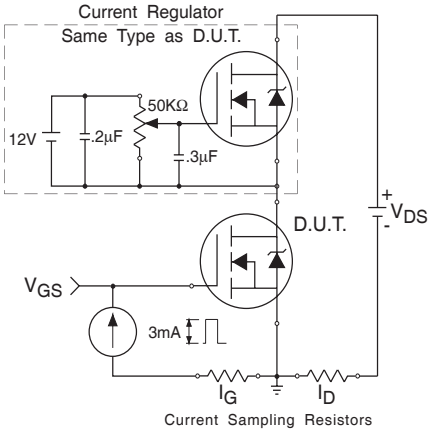
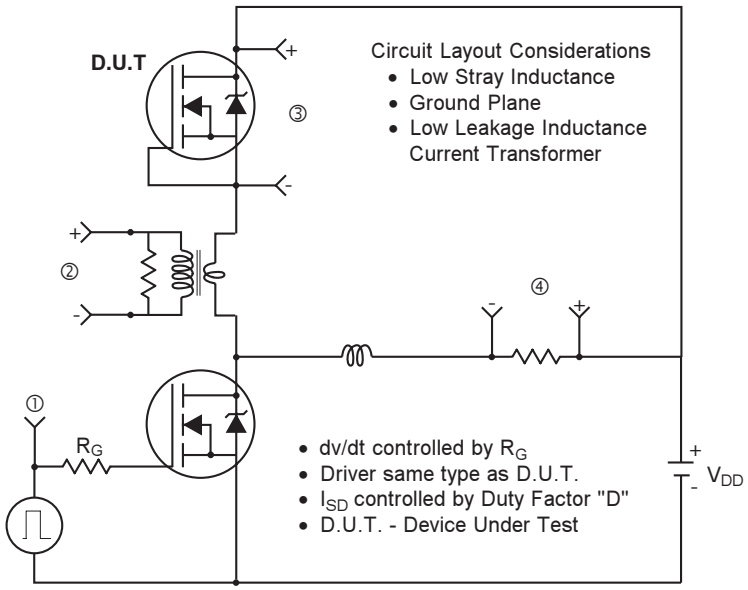
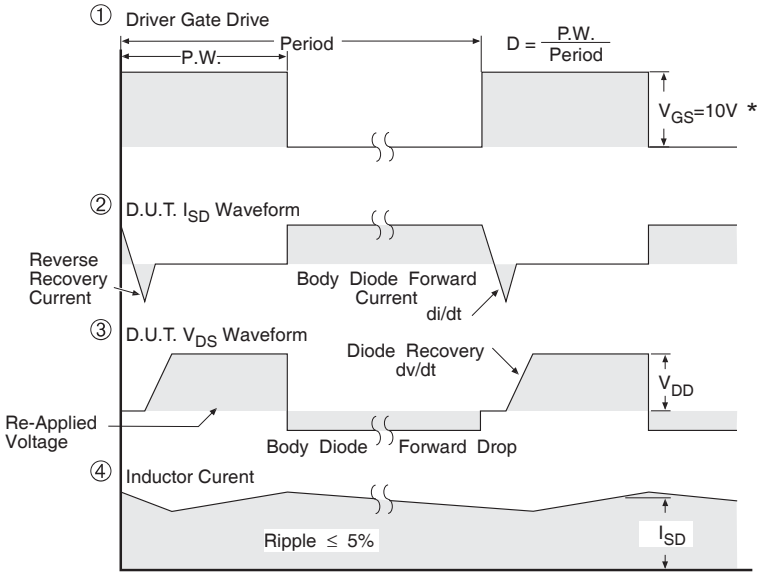


Fig 13b. Gate Charge Test Circuit

Peak Diode Recovery dv/dt Test Circuit



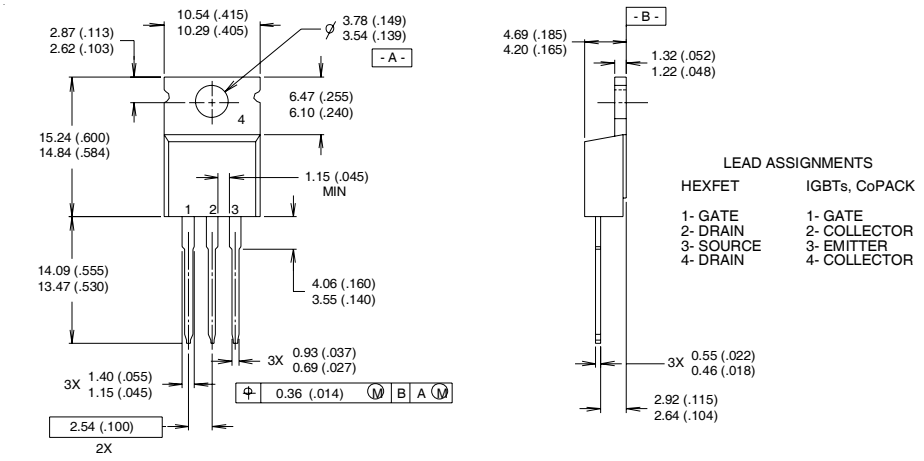


* V_{GS} = 5V for Logic Level Devices

Fig 14. For N-Channel HEXFET® power MOSFETs

TO-220AB Package Outline

Dimensions are shown in millimeters (inches)



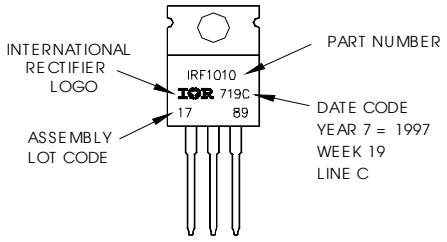
NOTES:

1 DIMENSIONING & TOLERANCING PER ANSI Y14.5M, 1982.
2 CONTROLLING DIMENSION : INCH
3 OUTLINE CONFORMS TO JEDEC OUTLINE TO-220AB.
4 HEATSINK & LEAD MEASUREMENTS DO NOT INCLUDE BURRS.

TO-220AB Part Marking Information

EXAMPLE: THIS IS AN IRF1010
LOT CODE 1789
ASSEMBLED ON WW 19, 1997
IN THE ASSEMBLY LINE "C"

Note: "P" in assembly line position indicates "Lead-Free"



Data and specifications subject to change without notice.

International
IOR Rectifier

IR WORLD HEADQUARTERS: 233 Kansas St., El Segundo, California 90245, USA Tel: (310) 252-7105
TAC Fax: (310) 252-7903
Visit us at www.irf.com for sales contact information.02/04